



ZXM61P02F

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C
-20V	600mΩ @ V _{GS} = -4.5V	-0.92A
	900mΩ @ V _{GS} = -2.7V	-0.75A

Description and Applications

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

- DC DC converters
- Power management functions
- · Disconnect switches
- Motor control

Features and Benefits

- · Fast switching speed
- Low on-resistance
- · Low threshold
- Low gate drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

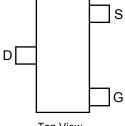
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

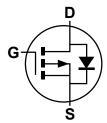
SOT23



Top View



Top View Pin Out



Equivalent Circuit

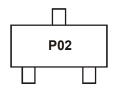
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXM61P02FTA	P02	7	8	3000 Units

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



P02 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V_{GS}	±12	V
Continuous Drain Current	V _{GS} = 4.5V	$T_A = +25^{\circ}C \text{ (Note 6)}$ $T_A = +70^{\circ}C \text{ (Note 6)}$	I _D	-0.9 -0.7	А
Pulsed Drain Current (Note 7)			I _{DM}	-4.9	Α
Continuous Source Current (Body Diode) (Note 6)			ls	-0.9	Α
Pulsed Source Current (Body Diode) (Note 7)			I _{SM}	-4.9	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

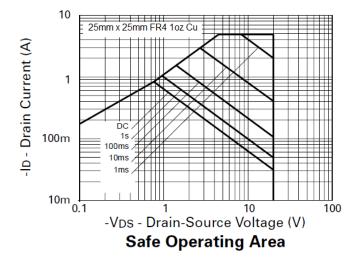
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	D-	625	mW
Linear Derating Factor	P _D	5	mW/°C
Power Dissipation (Note 6)	Б	806	mW
Linear Derating Factor	P _D	6.4	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	155	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C

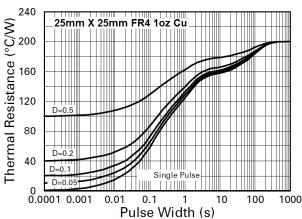
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- 6. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.

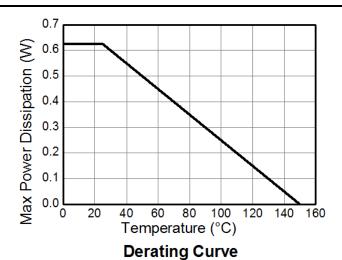
 7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10µs pulse current limited by maximum junction temperature.

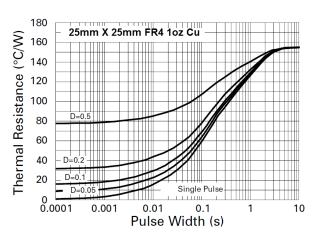
Thermal Characteristics





Transient Thermal Impedance





Transient Thermal Impedance



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

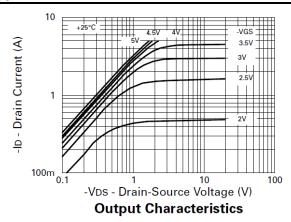
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-0.1	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-0.7	_	-1.5	V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	J			0.6	Ω	$V_{GS} = -4.5V$, $I_D = -0.61A$
Static Drain-Source On-Resistance (Note 6)	R _{DS (ON)}	_	_	0.9		$V_{GS} = -2.7V$, $I_D = -0.31A$
Forward Transconductance (Notes 8 and 10)	9 _{fs}	0.56	_	_	S	$V_{DS} = -10V, I_{D} = -0.31A$
Diode Forward Voltage (Note 8)	V_{SD}	_	_	-0.95	V	$T_J = +25^{\circ}C$, $I_S = -0.61A$, $V_{GS} = 0V$
Reverse Recovery Time (Note 10)	t _{rr}	_	14.9	_	ns	$T_J = +25^{\circ}C$, $I_F = -0.61A$,
Reverse Recovery Charge (Note 10)		_	5.6	_	nC	di/dt = 100A/µs
DYNAMIC CHARACTERISTICS (Note 10)					_	
Input Capacitance	C _{iss}	_	150	_		
Output Capacitance	Coss	_	70	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	30	_		I - I.OWITZ
Turn-On Delay Time (Note 9)	t _{d(on)}	_	2.9	_		
Turn-On Rise Time (Note 9)	tr	_	6.7	_	$V_{DD} = -110V$, $I_D = -0.93A$,	
Turn-Off Delay Time (Note 9)	t _{d(off)}	_	11.2	_	ns	$R_G\cong 6.2\Omega,\ R_D\cong 11\Omega,$
Turn-Off Fall Time (Note 9)	t _f	_	10.1	_		
Total Gate Charge (Note 9)	Qq	_	3.5	_		10/1/
Gate-Source Charge (Note 9)	Q _{gs}	_	0.5	_	nC $V_{DS} = -16V, V_{GS} = -4.5V,$ $I_{D} = -0.61A$	
Gate-Drain Charge (Note 9)	Q _{gd}	_	1.5	_		

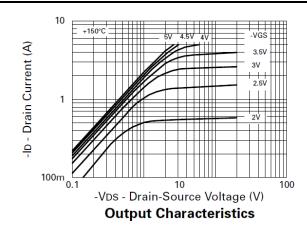
Notes:

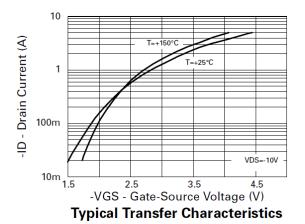
^{8.} Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

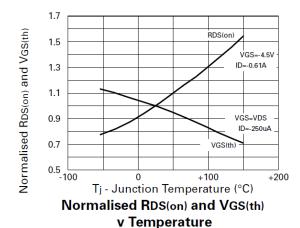


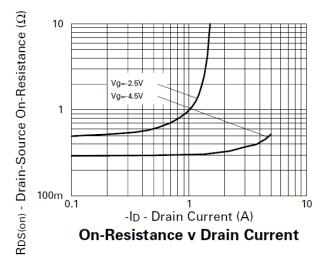
Typical Characteristics

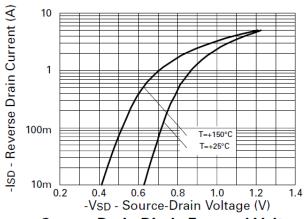








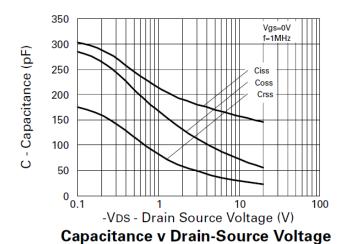


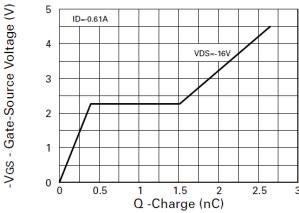


Source-Drain Diode Forward Voltage



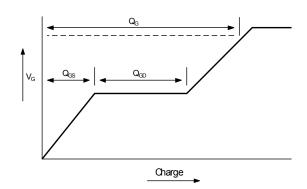
Typical Characteristics - continued



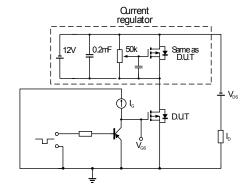


Gate-Source Voltage v Gate Charge

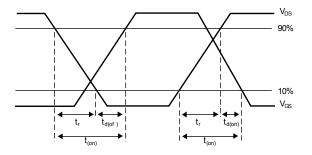
Test Circuits



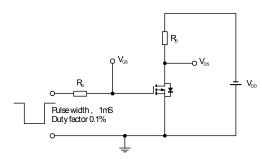
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

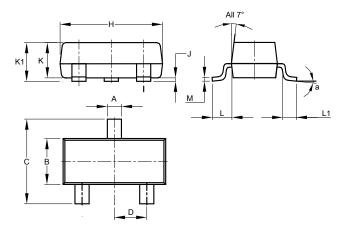


Switching time test circuit



Package Outline Dimensions

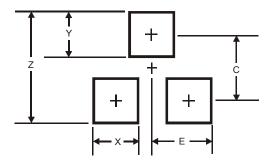
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890 1.00 0.975				
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	a 8°				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	0.8		
Y	0.9		
С	2.0		
Е	1.35		



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